

Oct. 02, 2003

Substitute for form 1449B/PTO			Complete if Known		
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)			Application Number	10/608,287	
			Filing Date	June 27, 2003	
			First Named Inventor	Yeo, <i>et al.</i>	
			Group Art Unit	2812	
			Examiner Name	TBD	
Sheet	2	of	2	Attorney Docket Number	TSM03-0421

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cita. No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.		
CC	J	HUANG, X., <i>et al.</i> "Sub-50 nm P-Channel FinFET," IEEE Transactions on Electron Devices, Vol. 48, No. 5 (May 2001) pp. 880-886.		2
CC	K	YANG, F.-L., <i>et al.</i> "35nm CMOS FinFETs," 2002 Symposium on VLSI Technology Digest of Technical Papers, (June 2002) pp. 109-110.		
CC	J	WONG, H.-S.P. "Beyond the Conventional Transistor," IBM Journal of Research and Development, Vol. 46, No. 2/3 (March/May 2002) pp. 133-167.		
CC	L	CHAU, R., <i>et al.</i> "Advanced Depleted-Substrate Transistors: Single-gate, Double-Gate and Tri-Gate," Extended Abstracts of the 2002 International Conference on Solid State Devices and Materials, (2002) pp. 68-69.		
CC	M	YANG, F.-L., <i>et al.</i> "25nm CMOS Omega FETs," International Electron Devices Meeting, Digest of Technical Papers, (December 2002) pp. 255-258.		
CC	N	COLINGE, J.P., <i>et al.</i> "Silicon-On-Insulator 'Gate -All-Around Device,'" International Electron Devices Meeting, (1990) pp. 595-598.		
CC	O	LEOBANDUNG, E., <i>et al.</i> "Wire-Channel and Wrap-Around-Gate Metal-Oxide-Semiconductor Field-Effect Transistors with a Significant Reduction of Short Channel Effects," Journal of Vacuum Science and Technology, Vol. B 15, No. 6, (November/December 1997) pp. 2791-2794.		

Examiner Signature	Chandra Chaudhari	Date Considered	3-05
--------------------	-------------------	-----------------	------

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Applicant's unique citation designation number (optional). *Applicant is to place a check mark here if English language Translation is attached. Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, DC 20231 *EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Applicant's unique citation designation number (optional). *Applicant is to place a check mark here if English language Translation is attached. This collection of information is required by 37 CFR 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 120 minutes to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P. O. Box 1450, Alexandria, VA 22313-1450.